



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-323 Plastic-Encapsulate DIODE

BAS70W SERIES

SCHOTTKY DIODE

FEATURES

Power dissipation

P_D : 200 mW ($T_{amb}=25^{\circ}C$)

Collector current

I_F : 70 mA

Collector-base voltage

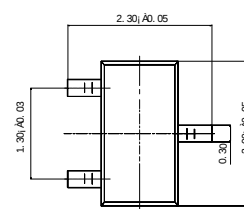
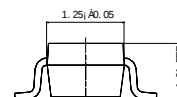
V_R : 70 V

Operating and storage junction temperature range

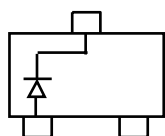
T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

SOT-323

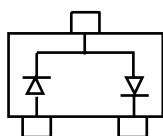
1. BASE
2. EMITTER
3. COLLECTOR



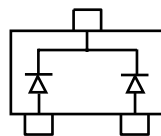
Unit: mm



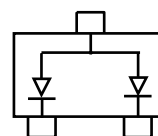
BAS70W Marking: K73



BAS70W-04 Marking: K74



BAS70W-05 Marking: K75



BAS70W-06 Marking: K76

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)R}$	$I_R = 10\mu A$	70		V
Reverse voltage leakage current	I_R	$V_R = 50V$		100	nA
Forward voltage	V_F	$I_F = 1mA$ $I_F = 15mA$		410 1000	mV
Diode capacitance	C_D	$V_R = 0V, f = 1MHz$		2	pF
Reveres recovery time	t_{rr}	$I_F = 10mA$ through $I_R = 10mA$ to $I_R = 1mA$		5	nS